

## PATENT ABSTRACTS OF JAPAN

(11)Publication number : 06-222388

(43)Date of publication of application : 12.08.1994

(51)Int.Cl.

G02F 1/136  
H01L 29/784

(21)Application number : 05-012065

(71)Applicant : FUJITSU LTD

(22)Date of filing : 28.01.1993

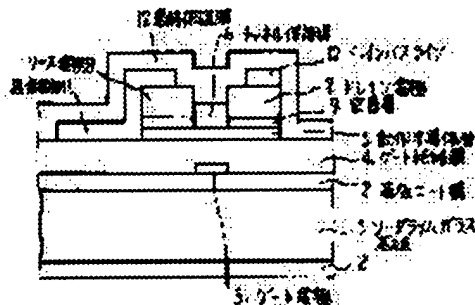
(72)Inventor : KOSUGI KIYOHISA  
WATABE JUNICHI  
SHIROKI IKUO

## (54) PRODUCTION OF THIN FILM TRANSISTOR MATRIX

## (57)Abstract:

PURPOSE: To obtain a substrate for a TFT matrix system LCD which is low in cost and does not degrade TFT characteristics from mixing of impurities in liquid crystal.

CONSTITUTION: In a glass substrate for the TFT matrix system LCD, a soda lime glass substrate 1 covered with a transparent insulating protective film 2 at one side or both sides of the glass substrate surface is used, the transparent insulating protective film 2 is formed by ALD method, the transparent insulating protective films 2 are simultaneously formed on both sides of the soda lime glass substrate 1 by ALD method. Further, after forming a gate electrode 3 on the soda lime glass substrate 1 covered with the transparent insulating protective films 2, a transparent insulating film is formed as a gate insulating film 4 by ALD method and the transparent insulating film is also formed by ALD method for a final protective film 12.



## LEGAL STATUS

[Date of request for examination]

[Date of sending the examiner's decision of rejection]

[Kind of final disposal of application other than the  
examiner's decision of rejection or application  
converted registration]

[Date of final disposal for application]

[Patent number]

[Date of registration]

[Number of appeal against examiner's decision of  
rejection][Date of requesting appeal against examiner's decision  
of rejection]

[Date of extinction of right]